

DIODE MODULE

DD(KD)60GB40/80

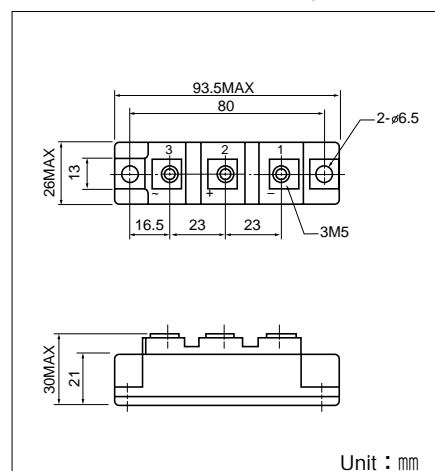
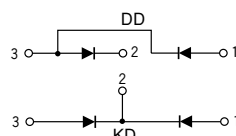
UL:E76102(M)

Power Diode Module **DD60GB** series are designed for various rectifier circuits. **DD60GB** has two diode chips connected in series and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 800V is available for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives



Maximum Ratings

(Tj=25°C unless otherwise specified)

Symbol	Item	Ratings		Unit
		DD60GB40	DD60GB80	
VRRM	Repetitive Peak Reverse Voltage	400	800	V
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	V

Symbol	Item		Conditions	Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180° conduction, Tc : 114°C	60	A
IF (RMS)	R.M.S. Forward Current		Single phase, half wave, 180° conduction, Tc : 114°C	95	A
IFSM	Surge Forward Current		1/2 cycle, 50/60Hz, peak value, non-repetitive	1100/1200	A
I²t	I²t		Value for one cycle of surge current	6000	A²S
Tj	Junction Temperature			-40 to +150	°C
Tstg	Storage Temperature			-40 to +125	°C
Viso	Isolation Voltage		A.C. 1minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	
	Mass			170	g

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
IRRM	Repetitive Peak Reverse Current, max.	at VDRM, single phase, half wave. Tj=150°C	20	mA
VFM	Forward Voltage Drop, max.	Forward current 180A, Tj=25°C, Inst. measurement	1.25	V
Rth(j-c)	Thermal Impedance, max.	Junction to case	0.50	°C/W

